NOT RECOMMENDED FOR NEW DESIGN **USE DMN61D9UDW**



DMN5L06DWK

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- **Dual N-Channel MOSFET**
- Low On-Resistance (1.0V Max)
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected up to 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMN5L06DWK-7	SOT363	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



DAB = Marking Code YM = Date Code Marking Y = Year ex: G = 2019 M = Month ex: 9 = September

Date Code Kev

Year	2006	2007	2008		2012	2013	2014	2015	2016	2017	2018	2019
Code	Т	U	V		Z	Α	В	С	D	E	F	G
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

DMN5L06DWK Document number: DS30930 Rev. 8 - 3



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DMN5L06DWK

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V_{DSS}	50	V
Gate-Source Voltage	V _{GSS}	±20	V
Drain Current Continuous	l le	305	mA
Pulsed (Note 6)		800	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	250	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	500	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

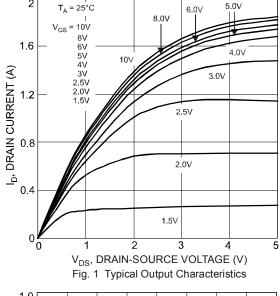
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	50	· —		V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current @ T _C = +25°C	1 _{DSS}	7		60	nΑ	$V_{DS} = 50V, V_{GS} = 0V$
				<u> 1</u>	μΑ	$V_{GS} = \pm 12V, V_{DS} = 0V$
Gate-Body Leakage	Igss	_		500	nΑ	$V_{GS} = \pm 10V, V_{DS} = 0V$
			X	50	nA	$V_{GS} = \pm 5V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.49		1.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
		_		3.0		$V_{GS} = 1.8V, I_D = 50mA$
Static Drain-Source On-Resistance	R _{DS(ON)}	_		2.5	Ω	$V_{GS} = 2.5V, I_D = 50mA$
			_	2.0		$V_{GS} = 5.0V, I_D = 50mA$
On-State Drain Current	ID(ON)	0.5	1.4	_	Α	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance	Y _{FS}	200	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$
Source-Drain Diode Forward Voltage	V _{SD}	0.5	_	1.4	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}		_	50	pF	V - 25V V - 0V
Output Capacitance	Coss		_	25	pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	_	5.0	pF	1 - 1.01/11/12
Gate Resistance	R _G	_	65		Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge	Q_G	_	0.4	_	nC	V 45V V 40V
Gate-Source Charge	Q _{GS}	_	0.1	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 0.25A$
Gate-Drain Charge	Q_{GD}	_	0.1	_	nC	ID = 0.25A
Turn-On Delay Time	t _{D(ON)}		2.1		ns	
Turn-On Rise Time	t _R	_	1.8		ns	$V_{DD} = 30V, V_{GS} = 10V,$
Turn-Off Delay Time	t _{D(OFF)}		14.4	_	ns	$R_G = 25\Omega$, $I_D = 0.2A$
Turn-Off Fall Time	t_{F}		8.4	_	ns	

Notes:

- Device mounted on FR-4 PCB.
 Pulse width ≤10μS, Duty Cycle ≤1%.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





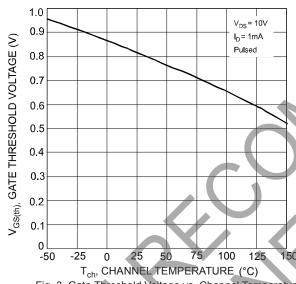


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

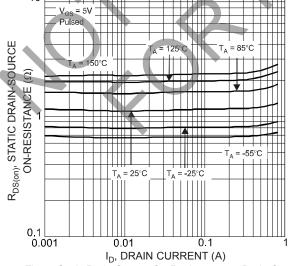
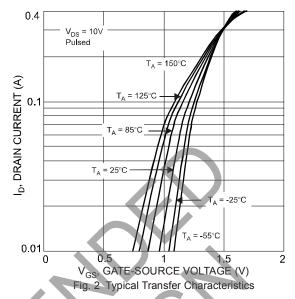


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current



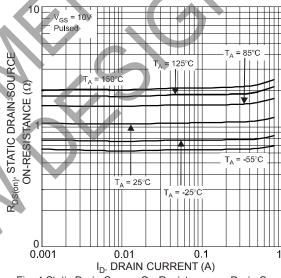


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

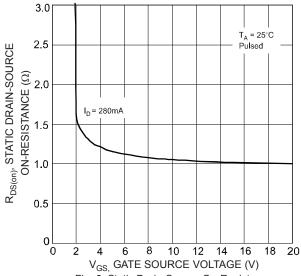


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage



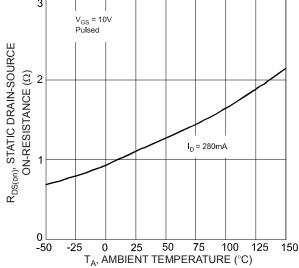


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

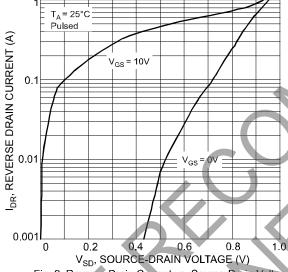
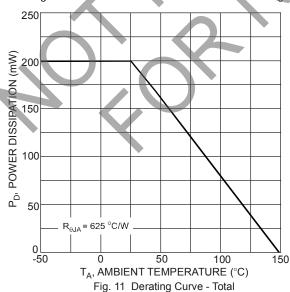


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage



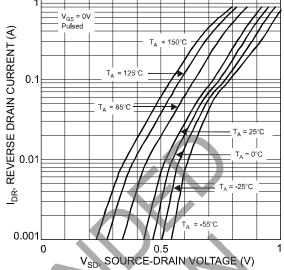


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

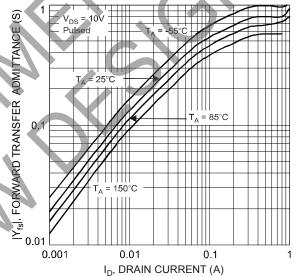


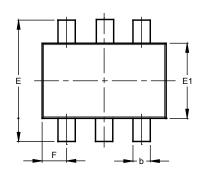
Fig.10 Forward Transfer Admittance vs. Drain Current

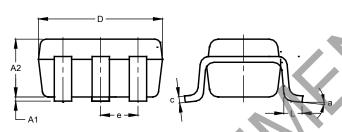


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



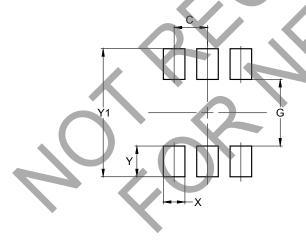


SOT363					
Dim	Min	Max	Тур		
A1	0.00	0.10	0.05		
A2	0.90	1.00	0.95		
Ь	0.10	0.30	0.25		
C	0.10	0.22	0.11		
D	1.80	2.20	2.15		
Ш	2.00	2.20	2.10		
E1	1.15	1.35	1.30		
е	0.650 BSC				
F	0.40	0.45	0.425		
4	0.25	0.40	0.30		
а	°	8°			
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



Dimensions	Value			
Dilliensions	(in mm)			
С	0.650			
G	1.300			
Х	0.420			
Y	0.600			
Y1	2 500			



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